

**FEATURES:**

- 0.5 MICRON CMOS Technology
- Typical  $t_{sk(o)}$  (Output Skew) < 250ps
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model ( $C = 200\text{pF}$ ,  $R = 0$ )
- $V_{cc} = 3.3\text{V} \pm 0.3\text{V}$ , Normal Range, or  $V_{cc} = 2.7\text{V}$  to  $3.6\text{V}$ , Extended Range
- CMOS power levels ( $0.4\mu\text{W}$  typ. static)
- Rail-to-rail output swing for increased noise margin
- Low Ground Bounce ( $0.3\text{V}$  typ.)
- Inputs (except I/O) can be driven by 3.3V or 5V components
- Available in SSOP and TSSOP packages

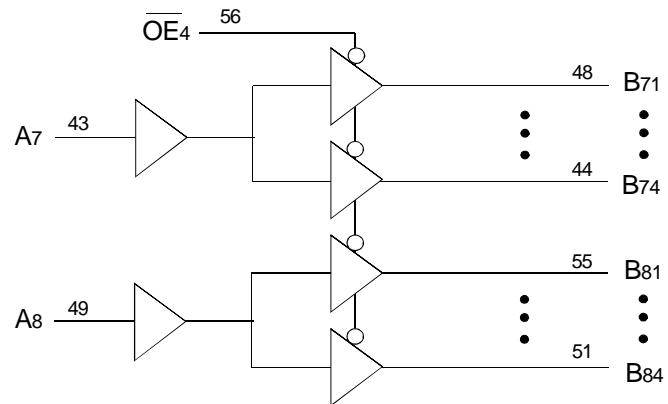
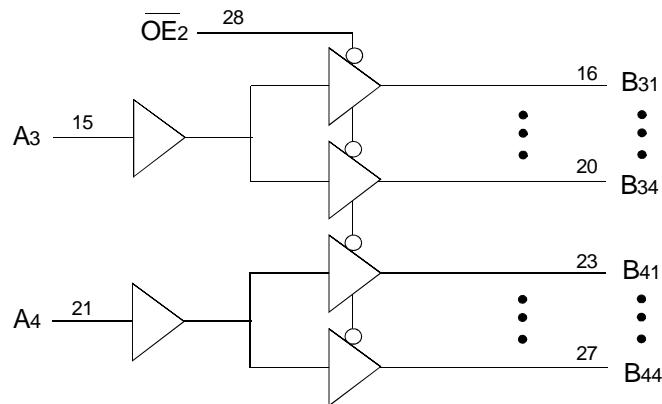
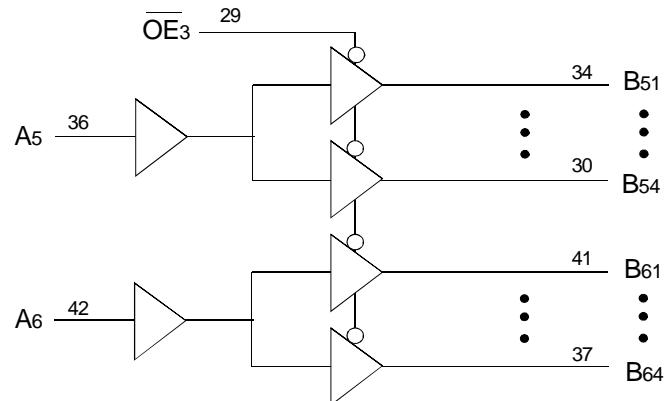
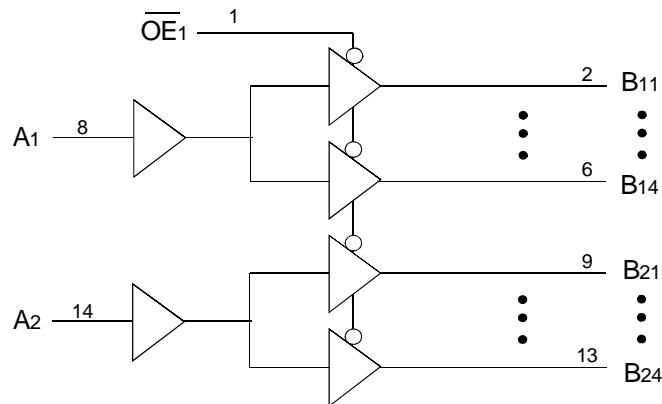
**DESCRIPTION:**

The FCT163344 is a 1:4 address/clock driver built using advanced dual metal CMOS technology. This high-speed, low power device provides the ability to fanout to memory arrays. Eight banks, each with a fanout of 4, and 3-state control provide efficient address distribution. One or more banks may be used for clock distribution.

The FCT163344 has series current limiting resistors. These offer low ground bounce, minimal undershoot and controlled output fall times, reducing the need for external series terminating resistors.

A large number of power and ground pins ensure reduced noise levels. All inputs are designed with hysteresis for improved noise margins.

The inputs of the FCT163344 can be driven from either 3.3V or 5V device. This feature allows the use of these devices as translators in a mixed 3.3V/5V supply system.

**FUNCTIONAL BLOCK DIAGRAM**


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**INDUSTRIAL TEMPERATURE RANGE**
**JANUARY 2004**

## PIN CONFIGURATION

OE1		1	56	OE4
B11		2	55	B81
B12		3	54	B82
GND		4	53	GND
B13		5	52	B83
B14		6	51	B84
VCC		7	50	VCC
A1		8	49	A8
B21		9	48	B71
B22		10	47	B72
GND		11	46	GND
B23		12	45	B73
B24		13	44	B74
A2		14	43	A7
A3		15	42	A6
B31		16	41	B61
B32		17	40	B62
GND		18	39	GND
B33		19	38	B63
B34		20	37	B64
A4		21	36	A5
VCC		22	35	VCC
B41		23	34	B51
B42		24	33	B52
GND		25	32	GND
B43		26	31	B53
B44		27	30	B54
OE2		28	29	OE3

SSOP/ TSSOP  
TOP VIEW

## ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Symbol	Description	Max	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
VTERM <sup>(3)</sup>	Terminal Voltage with Respect to GND	-0.5 to 7	V
VTERM <sup>(4)</sup>	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
TSTG	Storage Temperature	-65 to +150	°C
IOUT	DC Output Current	-60 to +60	mA

### NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. Vcc terminals.
3. Input terminals.
4. Outputs and I/O terminals.

## CAPACITANCE ( $T_A = +25^\circ\text{C}$ , $F = 1.0\text{MHz}$ )

Symbol	Parameter <sup>(1)</sup>	Conditions	Typ.	Max.	Unit
CIN	Input Capacitance	$V_{IN} = 0\text{V}$	3.5	6	pF
COUT	Output Capacitance	$V_{OUT} = 0\text{V}$	3.5	7	pF

### NOTE:

1. This parameter is measured at characterization but not tested.

## PIN DESCRIPTION

Pin Names	Description
$\bar{OE}_X$	3-State Output Enable Inputs (Active LOW)
A <sub>X</sub>	Inputs
B <sub>XX</sub>	3-State Outputs

## FUNCTION TABLE<sup>(1)</sup>

Inputs		Outputs
$\bar{OE}_X$	A <sub>X</sub>	B <sub>XX</sub>
L	L	L
L	H	H
H	X	Z

### NOTE:

1. H = HIGH Voltage Level  
L = LOW Voltage Level  
X = Don't Care  
Z = High-impedance

## DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial: TA = -40°C to +85°C, VCC = 2.7V to 3.6V

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
VIH	Input HIGH Level (Input pins)	Guaranteed Logic HIGH Level		2	—	5.5	V
	Input HIGH Level (I/O pins)			2	—	VCC+0.5	
VIL	Input LOW Level (Input and I/O pins)	Guaranteed Logic LOW Level		-0.5	—	0.8	V
I <sub>IH</sub>	Input HIGH Current (Input pins)	VCC = Max.	VI = 5.5V	—	—	±1	μA
	Input HIGH Current (I/O pins)		VI = VCC	—	—	±1	
I <sub>IL</sub>	Input LOW Current (Input pins)		VI = GND	—	—	±1	
	Input LOW Current (I/O pins)		VI = GND	—	—	±1	
I <sub>OZH</sub>	High Impedance Output Current	VCC = Max.	VO = VCC	—	—	±1	μA
I <sub>OZL</sub>	(3-State Output pins)		VO = GND	—	—	±1	
VIK	Clamp Diode Voltage	VCC = Min., I <sub>IN</sub> = -18mA		—	-0.7	-1.2	V
I <sub>ODH</sub>	Output HIGH Current	VCC = 3.3V, VIN = VIH or VIL, VO = 1.5V <sup>(3)</sup>		-36	-60	-110	mA
I <sub>ODL</sub>	Output LOW Current	VCC = 3.3V, VIN = VIH or VIL, VO = 1.5V <sup>(3)</sup>		50	90	200	mA
V <sub>OH</sub>	Output HIGH Voltage	VCC = Min.	I <sub>OH</sub> = -0.1mA	VCC-0.2	—	—	V
		VIN = VIH or VIL	I <sub>OH</sub> = -3mA	2.4	3	—	
		VCC = 3V	I <sub>OH</sub> = -8mA	2.4 <sup>(5)</sup>	3	—	
V <sub>OL</sub>	Output LOW Voltage	VCC = Min.	I <sub>OL</sub> = 0.1mA	—	—	0.2	V
		VIN = VIH or VIL	I <sub>OL</sub> = 16mA	—	0.2	0.4	
		VCC = 3V	I <sub>OL</sub> = 24mA	—	0.3	0.55	
		VIN = VIH or VIL	I <sub>OL</sub> = 24mA	—	0.3	0.5	
I <sub>OS</sub>	Short Circuit Current <sup>(4)</sup>	VCC = Max., VO = GND <sup>(3)</sup>		-60	-135	-240	mA
V <sub>H</sub>	Input Hysteresis	—		—	150	—	mV
I <sub>CCL</sub> I <sub>CCH</sub> I <sub>CCZ</sub>	Quiescent Power Supply Current	VCC = Max. VIN = GND or VCC		—	0.1	10	μA

### NOTES:

- For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at VCC = 3.3V, +25°C ambient.
- Not more than one output should be shorted at one time. Duration of the test should not exceed one second.
- This parameter is guaranteed but not tested.
- V<sub>OH</sub> = VCC-0.6V at rated current.

## POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$\Delta I_{CC}$	Quiescent Power Supply Current TTL Inputs HIGH	V <sub>CC</sub> = Max. V <sub>IN</sub> = V <sub>CC</sub> - 0.6V <sup>(3)</sup>		—	2	30	μA
I <sub>CCD</sub>	Dynamic Power Supply Current <sup>(4)</sup>	V <sub>CC</sub> = Max. Outputs Open $\overline{OE}_X$ = GND One Input Bit Toggling Four Output Bits Toggling 50% Duty Cycle	V <sub>IN</sub> = V <sub>CC</sub> V <sub>IN</sub> = GND	—	230	320	μA/ MHz
I <sub>C</sub>	Total Power Supply Current <sup>(6)</sup>	V <sub>CC</sub> = Max., Outputs Open f <sub>i</sub> = 10MHz 50% Duty Cycle $\overline{OE}_X$ = GND One Input Bit Toggling Four Output Bits Toggling	V <sub>IN</sub> = V <sub>CC</sub> V <sub>IN</sub> = GND	—	2.3	3.2	mA
		V <sub>CC</sub> = Max., Outputs Open f <sub>i</sub> = 10MHz 50% Duty Cycle $\overline{OE}_X$ = GND One Input Bit Toggling Four Output Bits Toggling	V <sub>IN</sub> = V <sub>CC</sub> - 0.6V V <sub>IN</sub> = GND	—	2.3	3.2	
		V <sub>CC</sub> = Max., Outputs Open f <sub>i</sub> = 2.5MHz 50% Duty Cycle $\overline{OE}_X$ = GND Eight Input Bits Toggling 32 Output Bits Toggling	V <sub>IN</sub> = V <sub>CC</sub> V <sub>IN</sub> = GND	—	4.6	6.4 <sup>(5)</sup>	
		V <sub>CC</sub> = Max., Outputs Open f <sub>i</sub> = 2.5MHz 50% Duty Cycle $\overline{OE}_X$ = GND Eight Input Bits Toggling 32 Output Bits Toggling	V <sub>IN</sub> = V <sub>CC</sub> - 0.6V V <sub>IN</sub> = GND	—	4.6	6.5 <sup>(5)</sup>	

## NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at V<sub>CC</sub> = 3.3V, +25°C ambient.

3. Per TTL driven input. All other inputs at V<sub>CC</sub> or GND.

4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.

5. Values for these conditions are examples of the I<sub>CC</sub> formula. These limits are guaranteed but not tested.

6.  $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

$$I_C = I_{CC} + \Delta I_{CC} D_{HNT} + I_{CCD} (f_{CP} N_{CP}/2 + f_i N_i)$$

I<sub>CC</sub> = Quiescent Current (I<sub>CCL</sub>, I<sub>CH</sub> and I<sub>CCZ</sub>)

$\Delta I_{CC}$  = Power Supply Current for a TTL High Input

D<sub>H</sub> = Duty Cycle for TTL Inputs High

N<sub>T</sub> = Number of TTL Inputs at D<sub>H</sub>

I<sub>CCD</sub> = Dynamic Current caused by an Input Transition Pair (HLH or LHL)

f<sub>CP</sub> = Clock Frequency for Register Devices (Zero for Non-Register Devices)

N<sub>CP</sub> = Number of Clock Inputs at f<sub>CP</sub>

f<sub>i</sub> = Input Frequency

N<sub>i</sub> = Number of Inputs at f<sub>i</sub>

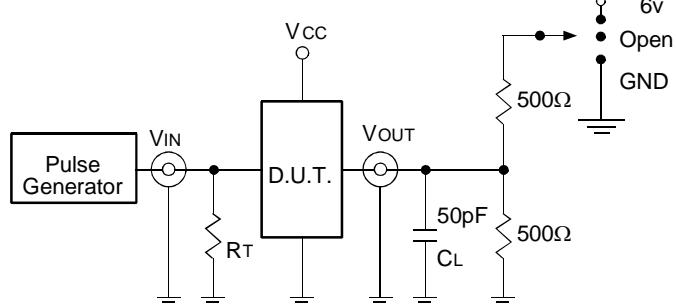
## SWITCHING CHARACTERISTICS OVER OPERATING RANGE<sup>(1)</sup>

Symbol	Parameter	Condition <sup>(2)</sup>	FCT163344A		FCT163344C		Unit
			Min. <sup>(3)</sup>	Max.	Min. <sup>(3)</sup>	Max.	
t <sub>PLH</sub>	Propagation Delay Ax to Bxx	C <sub>L</sub> = 50pF R <sub>L</sub> = 500Ω	1.5	4.8	1.5	4.3	ns
t <sub>PHL</sub>			1.5	6.2	1.5	5.8	ns
t <sub>PZH</sub>	Output Enable Time O <sub>E</sub> X to Bxx		1.5	5.6	1.5	5.2	ns
t <sub>PZL</sub>	Output Disable Time O <sub>E</sub> X to Bxx		—	0.5	—	0.35	ns
t <sub>SK(b)</sub>	Skew between outputs of the same bank and same package (same transition) <sup>(4,5)</sup>		—	0.5	—	0.5	ns
t <sub>SK(o)</sub>	Skew between outputs of all banks of the same package (A1 - A8 tied together) <sup>(4,5)</sup>						

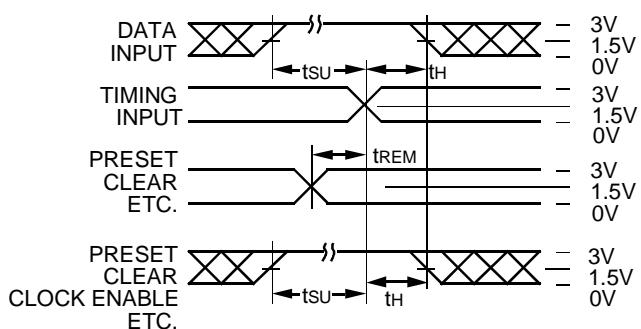
### NOTES:

1. Propagation Delays and Enable/Disable times are with V<sub>CC</sub> = 3.3V ±0.3V, Normal Range. For V<sub>CC</sub> = 2.7V to 3.6V, Extended Range, all Propagation Delays and Enable/Disable times should be degraded by 20%.
2. See test circuit and waveforms.
3. Minimum limits are guaranteed but not tested on Propagation Delays.
4. Skew between any two outputs, of the same package, switching in the same direction. This parameter is guaranteed by design.
5. This parameter is guaranteed but not tested. Skew is not guaranteed when V<sub>CC</sub> < 0.3V.

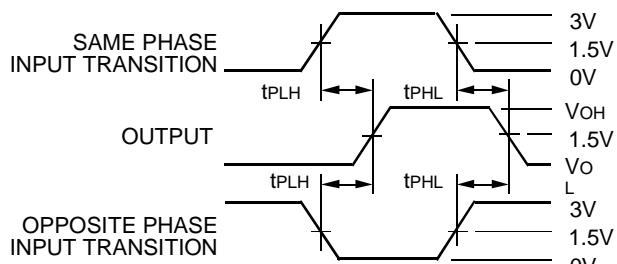
## TEST CIRCUITS AND WAVEFORMS



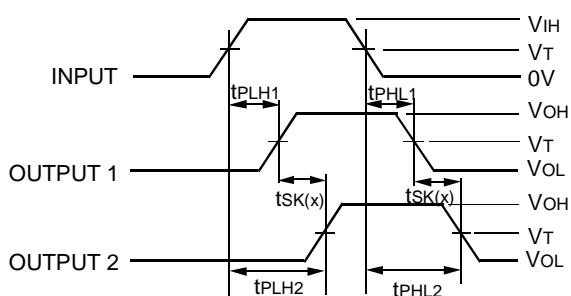
Test Circuits for All Outputs



Set-up, Hold, and Release Times



Propagation Delay

Output Skew -  $t_{SK(x)}$ 

## NOTES:

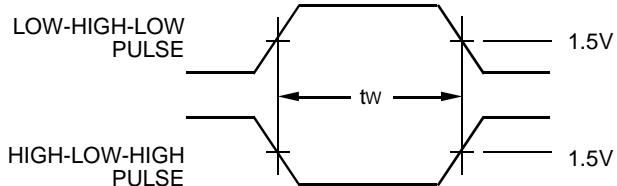
- For  $t_{SK(o)}$  OUTPUT1 and OUTPUT2 are any two outputs.
- For  $t_{SK(b)}$  OUTPUT1 and OUTPUT2 are in the same bank.

## SWITCH POSITION

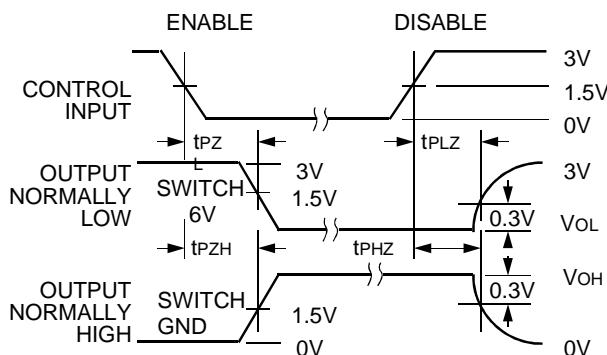
Test	Switch
Open Drain	6V
Disable Low	GND
Enable Low	Open
Disable High	Open
Enable High	GND
All Other Tests	Open

## DEFINITIONS:

$C_L$  = Load capacitance: includes jig and probe capacitance.  
 $R_T$  = Termination resistance: should be equal to  $Z_{OUT}$  of the Pulse Generator.



Pulse Width

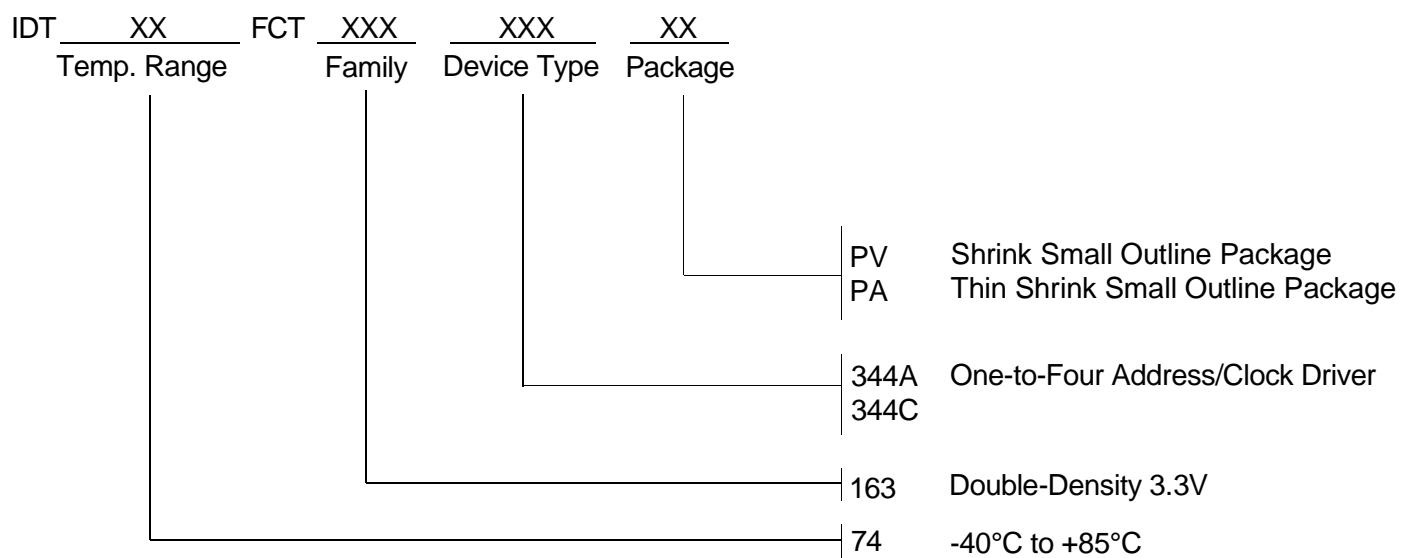


Enable and Disable Times

## NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- Pulse Generator for All Pulses: Rate  $\leq 1.0\text{MHz}$ ;  $t_f \leq 2.5\text{ns}$ ;  $t_r \leq 2.5\text{ns}$ .
- If  $V_{CC}$  is below 3V, input voltage swings should be adjusted not to exceed  $V_{CC}$ .

## ORDERING INFORMATION



## DATA SHEET DOCUMENT HISTORY

4/22/2002 Removed blank speed grade



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2975 Stender Way  
Santa Clara, CA 95054

*for SALES:*  
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